

Contents

1	Fundamentals of Noise in Optoelectronics	1
	Peter Seitz	
1.1	Introduction	1
1.2	Quantization of Electromagnetic Radiation, Electrical Charge, and Energy States in Bound Systems	2
1.3	Basic Properties of the Poisson Distribution	3
1.4	Interaction of Radiation and Matter	5
1.5	Noise Properties of Light Sources	6
1.5.1	Coherent Light (Single-Mode Lasers)	6
1.5.2	Thermal (Incandescent) Light Sources	6
1.5.3	Partially Coherent Light (Discharge Lamps)	7
1.5.4	Light Emitting Diodes	8
1.6	The Meaning of “Single-Photon Imaging”	9
1.7	Energy Band Model of Solid State Matter	11
1.8	Detection of Electromagnetic Radiation with Semiconductors	12
1.8.1	Quantum Efficiency and Band Structure	12
1.8.2	Thermal Equilibrium and Nonequilibrium Carrier Concentrations	13
1.8.3	Dark Current	14
1.8.4	Avalanche Effect and Excess Noise Factor	15
1.9	Electronic Detection of Charge	16
1.9.1	Basic Components of Electronics and their Noise Properties	17
1.9.2	Basic Circuits for Electronic Charge Detection	20
1.9.3	Conclusions for Single-Electron Charge Detection	21
1.10	Summary: Physical Limits of the Detection of Light	23
1.10.1	Sensitive Wavelength Range	23
1.10.2	Dark Current and Quantum Efficiency	24
1.10.3	Electronic Charge Detection	24
	References	25

2	Image Sensor Technology	27
	R. Daniel McGrath	
2.1	Program and a Brief History of Solid-State Image Sensors	27
2.2	Anatomy of an Image Sensor	28
2.3	Operation	33
2.4	Image Sensor Devices	35
2.5	Image Sensor Process Technology	39
2.6	Outlook for a Single Photon Process Technology	46
	References	47
3	Hybrid Avalanche Photodiode Array Imaging	49
	Hiroaki Aihara	
3.1	Introduction	49
3.2	Principle of Hybrid APD Operation	50
3.3	Single-pixel Large Format Hybrid APD	51
	3.3.1 Device Description	51
	3.3.2 Performance	53
	3.3.3 Application	55
3.4	Multipixel Hybrid APD Array	56
	3.4.1 Device Description	56
	3.4.2 Performance	60
	3.4.3 Application	61
3.5	Conclusions and Remaining Issues	62
	References	62
4	Electron Bombarded Semiconductor Image Sensors	63
	Verle Aebi and Kenneth Costello	
4.1	Introduction	63
4.2	Electron Bombarded Semiconductor Gain Process	65
4.3	Hybrid Photomultiplier EBS Image Sensors	66
	4.3.1 Hybrid Photomultiplier Gain and Noise Analysis	66
	4.3.2 Hybrid Photomultiplier Time Response	67
	4.3.3 Hybrid Photomultiplier Imagers	67
4.4	EBCCD and EBCMOS EBS Image Sensors	69
	References	71
5	Single-Photon Imaging Using Electron Multiplication in Vacuum ...	73
	Gert Nützel	
5.1	Introduction	73
5.2	The Photocathode	75
	5.2.1 The Working Principle of Photocathodes	75
	5.2.2 Multialkali Photocathodes	77
	5.2.3 III–V Photocathodes	79
5.3	Image Intensifiers	80
	5.3.1 Working Principle	80
	5.3.2 Applications	82

5.3.3	The Components of an Image Intensifier	83
5.3.4	Performance Characteristics	87
5.3.5	Special Image Intensifiers	94
5.4	Photomultiplier Tube	95
5.4.1	Working Principle	96
5.4.2	Applications.....	96
5.4.3	The Components of a PMT	97
5.4.4	Performance Characteristics	99
5.5	Conclusions and Outlook	102
	References.....	102
6	Electron-Multiplying Charge Coupled Devices – EMCCDs	103
	Mark Stanford Robbins	
6.1	Introduction.....	103
6.2	Harnessing Impact Ionisation for Ultra Sensitive CCD Imaging	104
6.3	The Electron Multiplying CCD Concept.....	104
6.3.1	Output Amplifier Noise	104
6.3.2	The Use of Multiplication Gain	106
6.3.3	Noise and Signal-to-Noise Ratio.....	109
6.3.4	Output Signal Distributions	110
6.4	Photon Counting with the EMCCD	112
6.5	Background Signal Generation	114
6.5.1	Dark Signal	114
6.5.2	Statistics of Dark Signal Generation.....	117
6.5.3	Spurious Charge Generation	117
6.6	Improving the Efficiency of Signal Generation	118
6.7	Concluding Comments	119
	References.....	120
7	Monolithic Single-Photon Avalanche Diodes: SPADs	123
	Edoardo Charbon and Matthew W. Fishburn	
7.1	A Brief Historical Perspective	123
7.2	Fundamental Mechanisms	124
7.2.1	SPAD Structure and Operation.....	124
7.2.2	Idle State and Avalanche Buildup.....	126
7.2.3	Quench, Spread, and Recharge	129
7.2.4	Example Waveforms.....	131
7.2.5	Pulse-Shaping	134
7.2.6	Uncorrelated Noise: Dark Counts.....	135
7.2.7	Correlated Noise: Afterpulsing and Other Time Uncertainties	136
7.2.8	Sensitivity: Photon Detection Probability	138
7.2.9	Wavelength Discrimination	141
7.3	Fabricating Monolithic SPADs	141
7.3.1	Vertical Versus Planar SPADs.....	141

7.3.2	Implementation in Planar Processes	142
7.3.3	SPAD Nonidealities	146
7.3.4	SPAD Array Nonidealities	146
7.4	Architecting SPAD Arrays	148
7.4.1	Basic Architectures	148
7.4.2	On-Chip Architecture	149
7.4.3	In-Column Architecture	150
7.4.4	In-Pixel Architecture	151
7.5	Trends in Monolithic Array Designs	153
7.6	Conclusions.....	154
	References.....	154
8	Single Photon CMOS Imaging Through Noise Minimization	159
	Boyd Fowler	
8.1	Introduction.....	159
8.2	Theory	161
8.2.1	QE and MTF	161
8.2.2	Photo-carrier Detection Probability.....	167
8.2.3	Additive Temporal Noise Systems.....	168
8.2.4	Uncorrelated Temporal Noise Sources	170
8.2.5	Correlated Temporal Noise Sources	174
8.3	Amplification and Bandwidth Control	175
8.3.1	Amplification	175
8.3.2	Bandwidth Control	179
8.4	Architectures	181
8.4.1	4T Pixel with Pinned Photodiode Column Level Amplification and CDS.....	181
8.4.2	4T CTIA Pixel with Pinned Photo Diode Column Level Amplification and CDS	184
8.4.3	Architecture Comparison.....	188
8.5	Low-Noise CMOS Image Sensor Optimization	189
8.5.1	Electrical	189
8.5.2	Optical.....	192
8.6	Conclusion.....	193
	References.....	194
9	Architectures for Low-noise CMOS Electronic Imaging.....	197
	Shoji Kawahito	
9.1	Introduction.....	197
9.2	Signal Readout Architectures.....	198
9.3	Correlated Samplings and their Noise Responses	201
9.3.1	Correlated Double Sampling and Correlated Multiple Sampling	201
9.3.2	Response of CDS and CMS to Thermal and 1/f Noises.....	203

- 9.4 Noise in Active-pixel CMOS Image Sensors Using Column CMS Circuits 207
- 9.5 Possibility of Single Photon Detection 211
 - 9.5.1 Single Photon Detection Using Quantization 211
 - 9.5.2 Condition for Single Photon Detection 214
- References 216
- 10 Low-Noise Electronic Imaging with Double-Gate FETs and Charge-Modulation Devices 219**

Yoshiyuki Matsunaga

 - 10.1 Introduction 219
 - 10.2 Double-Gate FET Charge Detector 220
 - 10.2.1 Floating Well Type 220
 - 10.2.2 Floating Surface Type 226
 - 10.3 CCD Image Sensor with Double-Gate FET Charge Detector 233
 - 10.3.1 Sensor Construction 233
 - 10.3.2 Feedback Charge Detector 234
 - 10.3.3 Evaluation 236
 - 10.3.4 Signal Processing 237
 - 10.4 Charge-Modulation Image Pixel Application 239
 - 10.4.1 Pixel Construction 242
 - 10.4.2 Operation 243
 - 10.4.3 Simulation 245
 - 10.4.4 Results 245
 - 10.4.5 Applications of Area Sensor 246
 - 10.5 Conclusions 248
 - References 248
- 11 Energy-Sensitive Single-Photon X-ray and Particle Imaging 249**

Christian Lotto

 - 11.1 Introduction 249
 - 11.1.1 Applications 250
 - 11.1.2 Basic Topology 251
 - 11.2 Particle Sensing Devices 251
 - 11.2.1 Direct Conversion Sensing Devices 252
 - 11.2.2 Scintillators Coupled to Sensing Devices for Visible Light 253
 - 11.3 Asynchronous Charge Pulse Detecting Circuits 254
 - 11.3.1 Charge Sensitive Amplifier 255
 - 11.3.2 Charge Sensitive Amplifier with Shaper 261
 - 11.3.3 Voltage Buffer with Shaper 269
 - 11.4 Voltage Pulse Processing Circuits 271
 - 11.4.1 Energy Discrimination Methods 272
 - 11.4.2 Information Readout 272
 - References 273

12	Single-Photon Detectors for Time-of-Flight Range Imaging	275
	David Stoppa and Andrea Simoni	
12.1	Introduction	275
12.2	Time-of-Flight Measuring Techniques and Systems	278
12.2.1	Time-of-flight System	278
12.2.2	Direct and Indirect Time Measuring Techniques	279
12.2.3	Optical Power Budget	281
12.2.4	D-TOF and I-TOF Noise Considerations	284
12.3	Single-Photon Sensors for 3D-TOF Imaging	286
12.3.1	Single-photon Detectors	286
12.3.2	Pixel Architectures for Single-photon TOF Imaging	288
12.3.3	Circuit Implementations for I-TOF Pixels	289
12.3.4	Circuit Implementations for D-TOF Pixels	291
12.3.5	State-of-the-art Time-resolved CMOS SPAD Pixel-array	293
12.4	Challenges and Future Perspectives	294
12.5	Conclusions	297
	References	298
13	Single-Photon Imaging for Astronomy and Aerospace Applications	301
	Pierre Magnan	
13.1	Introduction	301
13.2	Scientific Detectors in Astronomy and Space Applications	303
13.2.1	Scientific CCDs	303
13.3	Imaging Through the Atmosphere	309
13.4	Lucky Imaging Technique	311
13.5	Adaptive Optics	313
13.5.1	Principles	313
13.5.2	Wavefront Sensor Requirements and Detector Implementations	315
13.5.3	Infrared Detectors for Wavefront Sensor	319
13.6	Space LIDAR Applications	321
13.7	Concluding Remarks	324
	References	325
14	Exploiting Molecular Biology by Time-Resolved Fluorescence Imaging	329
	Francis Müller and Christof Fattinger	
14.1	Introduction: Time-Resolved Fluorescence as a Uniquely Sensitive Detection Method for the Analysis of Molecular Biology	329
14.1.1	Labeling of Specific Molecules by a Long- Lifetime Fluorophore	330

14.1.2	Integration of the Investigated Specimens in a Planar Array: Homogeneous and Heterogeneous Assays.....	331
14.1.3	Excitation of Multiple Specimens in the Array by Intense Light Pulses and Imaging of the Arrayed Specimens on an Image Sensor conceived for Time-Gated Readout of the Fluorescence Signal	332
14.1.4	Microarray Assays.....	333
14.2	Properties of the Ideal Fluorophore for Ultra-Sensitive Fluorescence Detection	334
14.3	Ruthenium Complexes	336
14.4	Applications in the Life Sciences.....	338
14.4.1	Assay for Drug Discovery.....	338
14.4.2	Assay for Point of Care Testing.....	341
14.5	Prospective Use of Ultra-Low-Noise CMOS Image Sensors for Time-Resolved Fluorescence Imaging	342
	References.....	344
	Index	345



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